Description

The 8V49NS0312 is a Clock Generator with four output dividers: three integer and one that is either integer or fractional. When used with an external crystal, the 8V49NS0312 generates high-performance timing geared towards the communications and datacom markets, especially for applications that demand extremely low phase noise, such as 10, 40, and 100GE.

The 8V49NS0312 provides versatile frequency configurations and output formats and is optimized to deliver excellent phase noise performance. The device delivers an optimum combination of high clock frequency and low phase noise performance, combined with high power supply noise rejection.

The 8V49NS0312 supports two types of output levels: LVPECL or LVDS on eleven of its outputs. In addition, there is a single LVCMOS output that has the option of providing a generated clock or acting as a reference bypass output.

The device can be configured to deliver specific output configurations under pin control only or additional configurations through an I^2C serial interface.

It is offered in a lead-free (RoHS6) 64-VFQFPN package.

Features

- Eleven differential LVPECL, LVDS outputs with programmable voltage swings
- One LVCMOS output
 - Input reference maybe bypassed to this output
- The clock input operates in full differential mode (LVDS, LVPECL) or single-ended LVCMOS mode
- Driven from a crystal or differential clock input
- 2.4-2.5GHz PLL frequency range supports Ethernet, SONET and CPRI frequency plans
- Four Integer output dividers with a range of output divide ratios (see *Table 7*)
- One Fractional Output divider can generate any desired output frequency
- Support of output power-down
- Excellent clock output phase noise <u>Offset</u> <u>Output Frequency</u> <u>Single-side Band Phase Noise</u> 100kHz 156.25MHz -143dBc/Hz
- Phase Noise RMS, 156.25MHz, 12kHz to 20MHz integration range: 110fs (maximum)
- Select configurations may be controlled via the use of control input pins without need for serial port access
- LVCMOS compatible I²C serial interface gives access to additional configurations either alone or in combination with the control input pins
- Single 3.3V supply voltage
- Lead-free (RoHS 6) 64-VFQFPN packaging
- -40°C to 85°C ambient operating temperature

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Block Diagram

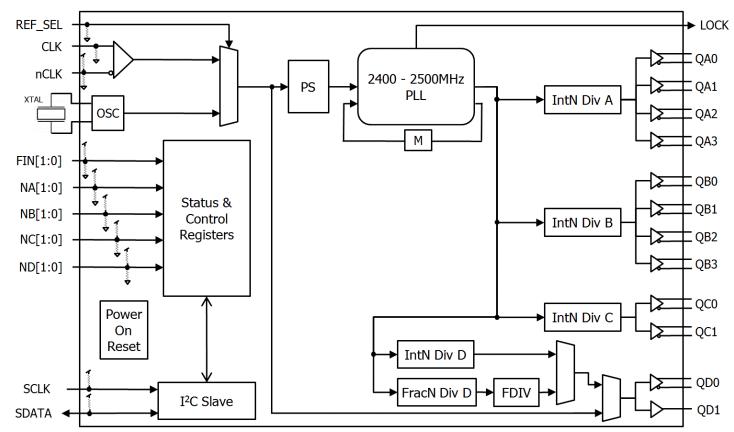
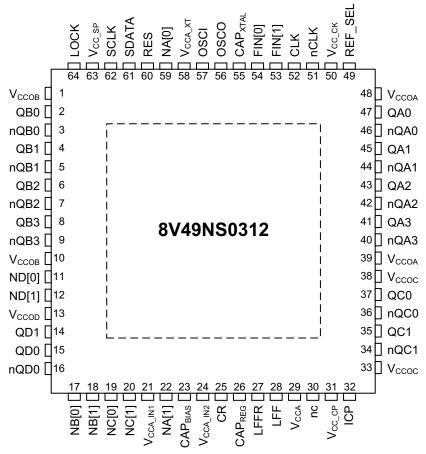


Figure 1: 8V49NS0312 Block Diagram



Pin Assignment



64-pin, 9mm x 9mm VFQFN Package

Pin Description and Pin Characteristic Tables

Table 1: Pin Descriptions^a

Number	Name	Ту	/pe	Description	
1	V _{CCOB}	Power		Power Supply Voltage for Output Bank B (3.3V).	
2	QB0	Output		Differential device cleak output pair LVPECL or LVPS with configurable amplitude	
3	nQB0	Output		 Differential device clock output pair. LVPECL or LVDS with configurable amplitude. 	
4	QB1	Output		Differential device cleak output pair LVPECL or LVPS with configurable amplitude	
5	nQB1	Output		 Differential device clock output pair. LVPECL or LVDS with configurable amp 	
6	QB2	Output		Differential device cleak extruct pair LV/DECL or LVDS with configurable emplitude	
7	nQB2	Output		 Differential device clock output pair. LVPECL or LVDS with configurable amplitude. 	
8	QB3	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.	
9	nQB3	Output			
10	V _{CCOB}	Power		Power Supply Voltage for Output Bank B (3.3V).	
11	ND[0]	Input	Pullup / Pulldown	Control Inputs for Output Bank D. 3-level signals. Refer to <i>Table 12</i> .	
12	ND[1]	Input	Pullup / Pulldown	Control Inputs for Output Bank D. 3-level signals. Refer to <i>Table 12</i> .	
13	V _{CCOD}	Power		Power Supply Voltage for Output Bank D (3.3V).	
14	QD1	Output		Single-ended output clock. LVCMOS output levels.	
15	QD0	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.	
16	nQD0	Output			
17	NB[0]	Input	Pullup / Pulldown	Control Inputs for Output Bank B. 3-level signals. Refer to <i>Table 10</i> .	
18	NB[1]	Input	Pullup / Pulldown	Control Inputs for Output Bank B. 3-level signals. Refer to <i>Table 10</i> .	
19	NC[0]	Input	Pullup / Pulldown	Control Inputs for Output Bank C. 3-level signals. Refer to <i>Table 11</i> .	
20	NC[1]	Input	Pullup / Pulldown	Control Inputs for Output Bank C. 3-level signals. Refer to <i>Table 11</i> .	
21	V _{CCA_IN1}	Power		Analog Power Supply Voltage for PLL (3.3V).	
22	NA[1]	Input	Pullup / Pulldown	Control Inputs for Output Bank A. 3-level signals. Refer to <i>Table 9</i> .	
23	CAP _{BIAS}	Analog		Internal VCO bias decoupling capacitor. Use a 4.7 μF capacitor between the CAP_{BIAS} terminal and V_{EE.}	
24	V _{CCA_IN2}	Power		Analog Power Supply Voltage for VCO (3.3V).	
25	CR	Analog		Internal VCO regulator decoupling capacitor. Use a $1\mu F$ capacitor between the CR and the V_{CCA} terminals.	
26	CAP _{REG}	Analog		Internal VCO regulator decoupling capacitor. Use a 4.7 μF capacitor between the CAP_{REG} terminal and V_{EE.}	

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Table 1: Pin Descriptions^aCont.

Number	Name	Ту	/pe	Description
27	LFFR	Analog		Ground return path pin for the PLL loop filter.
28	LFF	Output		Loop filter/charge pump output for the FemtoClock NG PLL. Connect to the external loop filter.
29	V _{CCA}	Power		Analog Power Supply Voltage for VCO (3.3V).
30	nc	-	-	No connect. Do not use.
31	V _{CC_CP}	Power		Analog Power Supply Voltage for PLL charge pump (3.3V).
32	ICP	Analog		Charge pump current input for PLL. Connect to LFF pin (28).
33	V _{CCOC}	Power		Power Supply Voltage for Output Bank C (3.3V).
34	nQC1	Output		
35	QC1	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
36	nQC0	Output		
37	QC0	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
38	V _{CCOC}	Power		Power Supply Voltage for Output Bank C (3.3V).
39	V _{CCOA}	Power		Power Supply Voltage for Output Bank A (3.3V).
40	nQA3	Output		
41	QA3	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
42	nQA2	Output		
43	QA2	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
44	nQA1	Output		
45	QA1	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
46	nQA0	Output		
47	QA0	Output		Differential device clock output pair. LVPECL or LVDS with configurable amplitude.
48	V _{CCOA}	Power		Power Supply Voltage for Output Bank A (3.3V).
49	REF_SEL	Input	Pulldown	Selects Input Reference source. LVCMOS interface levels. 0 = Crystal input on pins OSCI, OSCO (default) 1 = Reference clock input on pins CLK, nCLK
50	V _{CC_CK}	Power		Power Supply Voltage for input CLK, nCLK (3.3V).
51	nCLK	Input	Pullup/ Pulldown	Inverting differential clock input. Internal resistor bias to $V_{CC_CK.}$
52	CLK	Input	Pulldown	Non-inverting differential clock input.
53	FIN[1]	Input	Pullup / Pulldown	Control Inputs for Input Reference Frequencies. 3-level signals. Refer to Table 5.
54	FIN[0]	Input	Pullup / Pulldown	Control Inputs for Input Reference Frequencies. 3-level signals. Refer to <i>Table 5</i> .
55	CAP _{XTAL}	Analog		Crystal oscillator circuit decoupling capacitor. Use a 4.7 μ F capacitor between the CAP _{XTAL} and the V _{EE} terminals.

Table 1: Pin Descriptions^aCont.

Number	Name	Ту	/pe	Description
56	OSCO	Output		Crystal oscillator interface.
57	OSCI	Input		Crystal oscillator interface.
58	V _{CCA_XT}	Power		Analog Power Supply Voltage for the Crystal Oscillator (3.3V).
59	NA[0]	Input	Pullup / Pulldown	Control Inputs for Output Bank A. 3-level signals. Refer to <i>Table 9</i> .
60	RES	Analog		Connect a 2.8 k Ω (1%) resistor to V _{EE} for output current calibration.
61	SDATA	I/O	Pullup	I ² C data Input/Output: LVCMOS interface levels. Open Drain Pin.
62	SCLK	Input	Pullup	I ² C clock input. LVCMOS interface levels.
63	V _{CC_SP}	Power		Power Supply Voltage for the I ² C port (3.3V).
64	LOCK	Output		Lock status output. LVCMOS interface levels. Logic Low = PLL not locked Logic High = PLL locked
ePad	V _{EE}	Power		Negative supply. Exposed pad must be connected to ground

a. *Pulldown* and *Pullup* refer to internal input resistors. See *Table 2, Input Characteristics,* for typical values.

Table 2: Input Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance ^a			3.5		pF
R _{PULLDOWN}	Input Pulldown Resistor			51		kΩ
R _{PULLUP}	Input Pullup Resistor			51		kΩ

a. This specification does not apply to OSCI and OSCO pins.

Table 3: Output Characteristics

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
R _{OUT} Output Impedance	Output	LOCK			20		Ω
	QD1	$V_{CC}^{a} = 3.3V \pm 5\%$		30		Ω	

a. V_{CC} denotes V_{CC_SP}, V_{CCOD}.



Principles of Operation

The 8V49NS0312 can be locked to either an input reference clock or a 10MHz to 50MHz fundamental-mode crystal and generate a wide range of synchronized output clocks. Lock status may be monitored via the LOCK pin.

It could be used for example in either the transmit or receive path of Synchronous Ethernet or SONET/SDH equipment.

The 8V49NS0312 accepts a differential or single-ended input clock ranging from 5MHz up to 1GHz. It generates up to twelve output clocks with up to four different output frequencies, ranging from 10.91MHz up to 2.5GHz.

The device outputs are divided into 4 output banks. Each bank supports conversion of the input frequency to a different output frequency: one independent or integer-related output frequency on Bank D (QD[0:1]) and three more integer-related frequencies on Bank A (QA[0:3]), Bank B (QB[0:3]) and Bank C (QC[0:1]). All outputs within a bank will have the same frequency.

The device is programmable through an I²C serial interface or control input pins.

Pin versus Register Control

The 8V49NS0312 can be configured by the use of input control pins and/or over an I²C serial port. The pins / registers used to control each function are shown in Table 4. At power-up, control of each function is via the control input pins. Access over the serial port can change each function individually to be controlled by registers. This allows for any mixture of register or pin control. However any of the indicated functions can only be controlled by register or by pin at any given time, not by both. Use of register control will allow access to a wider range of configuration options, but values are lost on power-down.

Function	Control Select Bit	Control Input Pins	Register Fields Affected
Prescaler & PLL Feedback Divider	FIN_CTL	FIN[1:0]	PS[5:0], FDP M[8:0]
Bank A Divider & Output Type	NA_CTL	NA[1:0]	NA_DIV, PD_A, EN_A, PD_QAx, STY_QAx, AMP_QAx[1:0]
Bank B Divider & Output Type	NB_CTL	NB[1:0]	NB_DIV, PD_B, EN_B, PD_QBx, STY_QBx, AMP_QBx[1:0]
Bank C Divider & Output Type	NC_CTL	NC[1:0]	NC_DIV, PD_C, EN_C, PD_QCx, STY_QCx, AMP_QCx[1:0]
Bank D Divider & Output Type	ND_CTL	ND[1:0]	ND[5:0], ND_FINT[3:0], ND_FRAC[23:0], ND_DIVF[1:0], ND_SRC[1:0], PD_D, EN_D, PD_QDx, STY_QD0, AMP_QD0[1:0]

Table 4: Control of Specific Functions

Changes to the control input pins while the part is active are allowed, but can not be guaranteed to be glitch-free. It is recommended that any such changes be performed by disabling the outputs using the I^2C -accessible registers, then re-enabling once changes are completed. Also, the output dividers, which are synchronized on power-up will not be re-synchronized without an explicit access to the INIT_CLK register bit over the I^2C interface.

Any change to the output dividers performed over the I²C interface must be followed by an assertion of the INIT_CLK register bit to force the loading of the new divider values, as well as to synchronize the output dividers.

Input Clock Selection (REF_SEL)

The 8V49NS0312 needs to be provided with an input reference frequency either from its crystal input pins (OSCI, OSCO) or its reference clock input pins (CLK, nCLK). The REF_SEL input pin controls which source is used.

The crystal input on the 8V49NS0312 is capable of being driven by a parallel-resonant, fundamental mode crystal with a frequency of 10MHz to 50MHz.

The crystal input also supports being driven by a single-ended crystal oscillator or reference clock, but only a frequency from 10MHz to 50MHz may be used on these pins.

The reference clock input accepts clocks with frequencies ranging from 5MHz up to 1GHz. Each input can accept LVPECL, LVDS, LVHSTL, HCSL or LVCMOS inputs using 2.5V or 3.3V logic levels as shown in the Applications Information section of this datasheet.

Prescaler and PLL Configuration

When the input frequency (f_{IN}), whether generated by a crystal or clock input is known, and the desired PLL operating frequency has been determined, several constraints need to be met:

- The Phase / Frequency Detector operating frequency (f_{PFD}) must be within the specified limits shown in Table 28. This is controlled by selecting an appropriate doubler (FDP) and prescaler (PS) value. If multiple values are possible, a higher f_{PFD} will provide better phase noise performance.
- The VCO operating frequency (f_{VCO}) must be within the specified limits shown in Table 28. This is controlled by selecting an appropriate
 PLL feedback Divider (M) value. Note that it may be necessary to chose a different prescaler value if the limits can not be met by the
 available values of M. It may also be necessary to select an appropriate input frequency value.

Several preset configurations may be selected directly from the FIN[1:0] control input pins. These configurations are based on a particular input frequency f_{IN} and a particular f_{VCO} (see Table 5). These selections apply whether the input frequency is provided from the crystal or reference clock inputs

FIN[1]	FIN[0]	f _{IN} (MHz)	f _{VCO} (MHz)
High	High	38.88	2488.32
High	Middle ^a	38.4	2457.6
High	Low	31.25	2500
Middle	High	312.5	2500
Middle	Middle	125	2500
Middle	Low	156.25	2500
Low	High	100	2500
Low	Middle	25	2500
Low	Low	50	2500

Table 5: Input Selection Control

a. A 'middle' voltage level is defined in Table 22. Leaving the input pin open will also generate this level via a weak internal resistor network.

Alternatively the user may directly access the registers for M, FDP & PS over the serial interface for a wider range of options. See Table 6 for some examples.

Inputs do not support transmission of spread-spectrum clocking sources. Since this family is intended for high-performance applications, it will assume input reference sources to have stabilities of <u>+</u>100ppm or better.

f _{IN} (MHz)	PS	FDP	f _{PFD} (MHz)	М	PLL Operating Frequency (MHz)
25	1	2	50	50	2500
39.0625	1	2	78.125	32	2500
50	1	2	100	25	2500
100	1	1	100	25	2500
125	1	1	125	20	2500
156.25	1	1	156.25	16	2500
200	2	1	100	25	2500
250	2	1	125	20	2500
312.5	2	1	156.25	16	2500
400	4	1	100	25	2500
500	4	1	125	20	2500
625	4	1	156.25	16	2500
19.44	1	2	38.88	64	2488.32
38.88	1	2	77.76	32	2488.32
38.4	1	2	76.8	32	2457.6

Table 6: PLL Frequency Control Examples

PLL Loop Bandwidth

The 8V49NS0312 uses one external capacitor of fixed value to support its loop bandwidth. A fixed loop bandwidth of approximately 200kHz is provided.

Output Divider Frequency Sources

Output dividers associated with Banks A, B & C take their input frequency directly from the PLL.

Bank D also has the option to bypass the input frequency (after mux) directly to the output.

Integer Output Dividers (Banks A, B, C, and D)

The 8V49NS0312 supports four integer output dividers: one per output bank. Each integer output divider block independently supports one of several divide ratios as shown in their respective register descriptions (*Table 15, Table 16, Table 17* or *Table 18*). Select divide ratios can be chosen directly from the control input pins for that particular output bank. The remaining ratios can only be selected via the serial interface. Bank D may choose whether to use the integer divider or a separate fractional divider to generate the output.

Some example output frequencies are shown in *Table 7* for the minimum f_{VCO} (2400MHz), the maximum f_{VCO} (2500MHz) and two other common VCO frequencies. With appropriate input frequencies and configuration selections, any f_{VCO} and f_{OUT} between the minimum and maximum can be generated.

	f _{OUT} (MHz)						
Divide Ratio	f _{VCO} = 2400MHz	f _{VCO} = 2457.6MHz	f _{VCO} = 2488.32MHz	f _{VCO} = 2500MHz			
1	2400	2457.6	2488.32	2500			
2	1200	1228.8	1244.16	1250			
4	600	614.4	622.08	625			
5	480	491.52	497.664	500			
6	400	409.6	414.72	416.667			
8	300	307.2	311.04	318.75			
9	266.667	273.07	276.48	277.78			
10	240	245.76	248.832	250			
12	200	204.8	207.36	208.333			
16	150	153.6	155.52	156.25			
18	133.333	136.533	138.24	138.889			
20	120	122.88	124.416	125			
25	96	98.3	99.53	100			
32	75	76.8	77.76	78.125			
36	66.667	68.267	69.12	69.444			
40	60	61.44	62.208	62.5			
50	48	49.152	49.766	50			
64	37.5	38.4	38.88	39.063			
72	33.333	34.133	34.56	34.722			
80	30	30.72	31.104	31.25			
100	24	24.576	24.883	25			
128	18.75	19.2	19.44	19.531			
160	15	15.36	15.552	15.625			
200	12	12.29	12.44	11.36			
220	10.91	11.17	11.31	11.36			

Table 7: Integer Output Divider Control Examples



Fractional Output Divider (Bank D)

For the fractional output divider in Bank D, the output divide ratio is given by:

$$f_{OUT} = \frac{I_{VCO}}{2 \times \left(FINT + \frac{FRAC}{2^{24}}\right) \times (FDIV)}$$

Where,

- FINT = Integer Part: 5, 6, ...(2⁴-1) given by ND_FINT[3:0]
- FRAC = Fractional Part: 0, 1, 2, ...(2²⁴-1)- given by ND_FRAC[23:0]
- FDIV = post-divider: 1, 2 or 4- given by ND_DIVF[1:0]

This provides a frequency range of 20MHz to 312.5MHz.

Output Drivers

Each of the four output banks are provided with pin or register-controlled output drivers. Differential outputs may be individually selected as LVDS, LVPECL or POWER-DOWN. When powered down, both outputs of the differential output pair will drive a logic-high level, and the single-ended QD1output will be in Hi-Z state.

The differential outputs may individually choose one of several different output voltage swings: 350mV, 500mV or 750mV, measured single-ended.

Note that under pin-control, all differential outputs within an output bank will assume the same configuration. Pin-control does not allow configuration of individual outputs within a bank.

Pin Control of the Output Frequencies and Protocols

See *Table 8, Table 9, Table 10, Table 11* and *Table 12*, for pin-control settings. All of the output frequencies assume f_{VCO} = 2500MHz. With different f_{VCO} configurations, the pins may still be used to select the indicated divide ratios for each bank, but the f_{OUT} will be different.

Note that the control pins do not affect the internal register values, but act directly on the output structures. So register values will not change to match the control input pin selections.

Each output bank may be powered-up / down and enabled / disabled by register bits. In the disabled state, an output will drive a logic low level. The default state is all outputs enabled. Pin-control does not require register access to enable the outputs. Additionally, individual outputs within a bank may be powered up / down.

Table 8: Definition of Output Disabled / Power-down

OUTPUT CONDITION	Q _{MN} ^a	nQ _{MN} b	QD1
DISABLED (register-control only)	LOW	HIGH	LOW
POWER-DOWN (pin-control or register-control)	HIGH	HIGH	Hi-Z

a. Q_{MN} refers to output pins QA[0:3], QB[0:3], QC[0:1] and QD0.

b. nQ_{MN} refers to output pins nQA[0:3], nQB[0:3], nQC[0:1] and nQD0.

Table 9: Bank A Divider/ Driver Pin-Control

(3-level control signals)

NA[1]	NA[0]	Output Type	Divide Ratio	f _{оuт} (MHz)
Low	Low	LVPECL ^a	16	156.25
Low	Middle	LVPECL	20	125
Low	High	LVPECL	25	100
Middle	Low	LVPECL	100	25
Middle	Middle	POWER-DOWN ^b	-	-
Middle	High	LVDS ^c	16	156.25
High	Low	LVDS	20	125
High	Middle	LVDS	25	100
High	High	LVDS	50	50

a. Under pin control, all outputs of the bank are LVPECL using 750mV output swing.b. No active receivers should be connected to QA outputs.

c. Under pin control, all outputs of the bank are LVDS using 350mV output swing.

Table 10: Bank B Divider/ Driver Pin-Control (3-level control signals)

NB[1]	NB[0]	Output Type	Divide Ratio	f _{OUT} (MHz)
Low	Low	LVPECL ^a	16	156.25
Low	Middle	LVPECL	20	125
Low	High	LVPECL	25	100
Middle	Low	LVPECL	100	25
Middle	Middle	POWER-DOWN	-	-
Middle	High	LVDS ^c	16	156.25
High	Low	LVDS	20	125
High	Middle	LVDS	25	100
High	High	LVDS	50	50

a. Under pin control, all outputs of the bank are LVPECL using 750mV output swing.b. No active receivers should be connected to QB outputs.

c. Under pin control, all outputs of the bank are LVDS using 350mV output swing.

Table 11: Bank C Divider/ Driver Pin-Control (3-level control signals)

NC[1]	NC[0]	Output Type	Divide Ratio	f _{OUT} (MHz)
Low	Low	LVPECL ^a	8	312.5
Low	Middle	LVPECL	16	156.25
Low	High	LVPECL	20	125
Middle	Low	LVPECL	100	25
Middle	Middle	POWER-DOWN ^b		-
Middle	High	LVDS ^c	20	125
High	Low	LVDS	25	100
High	Middle	LVDS	50	50
High	High	LVDS	100	25

a. Under pin control, all outputs of the bank are LVPECL using 750mV output swing.b. No active receivers should be connected to QC outputs.

c. Under pin control, all outputs of the bank are LVDS using 350mV output swing.

Table 12: Bank D Divider/ Driver Pin-Control (3-level control signals)

ND[1]	ND[0]	QD0 Output Type	QD1 Output Type	Divide Ratio	f _{OUT} (MHz)
Low	Low	LVDS ^a	Hi-Z	25	100
Low	Middle	LVDS	Hi-Z	50	50
Low	High	LVDS	Hi-Z	18.75 ^b	133.333
Middle	Low	LVDS	Hi-Z	37.5 ^b	66.667
Middle	Middle	POWER-DOWN ^c	Hi-Z	-	-
Middle	High	POWER-DOWN ^c	LVCMOS	75	33.333
High	Low	LVDS	Hi-Z	100	25
High	Middle	LVDS	Hi-Z	20	125
High	High	LVDS	LVCMOS	1	f _{IN} d

a. Under pin control, all outputs of the bank are LVDS using 350mV output swing.

b. Generated from Fractional divider.

c. No active receivers should be connected to QD0 output.

d. This bypasses the input frequency directly to the output.

Device Start-up and Reset Behavior

The 8V49NS0312 has an internal power-on reset (POR) circuit. The POR circuit will remain active for a maximum of 175msec after device power-up.

While in the reset state (POR active), the device will operate as follows:

- All registers will return to & be held in their default states as indicated in the applicable register description.
- All internal state machines will be in their reset conditions.
- The serial interface will not respond to read or write cycles.
- All clock outputs will be enabled.
- Lock status will be cleared.

Upon the internal POR circuit expiring, the device will exit reset and begin self-configuration.

Self-configuration will consist of loading appropriate default values into each register as indicated by the control input pins and the defaults indicated in the register descriptions.

Once the full configuration has been loaded, the device will respond to accesses on the serial port and will attempt to lock the PLL to the input frequency and begin operation. Once the PLL is locked, all the outputs derived from it will be synchronized.

Serial Control Port Description

Serial Control Port Configuration Description

The device has a serial control port capable of responding as a slave in an I^2C compatible configuration at a base address of 1101100b, to allow access to any of the internal registers for device programming or examination of internal status.

All registers are configured to have default values. See the specifics for each register for details. Default values for registers will be set after reset by the configuration pins.

Any changes to the configuration pins will result in the appropriate register(s) being changed to reflect the new pin-controlled setup. Any such change while the part is operating may result in glitches on output clocks, even if those particular clocks are not being reconfigured.

I²C Mode Operation

The I^2C interface is designed to fully support v1.2 of the I^2C Specification for Normal and Fast mode operation. The device acts as a slave device on the I^2C bus at 100kHz or 400kHz using a fixed base address of 1101100b. The interface accepts byte-oriented block write and block read operations. One address byte specifies the register address of the byte position of the first register to write or read. Data bytes (registers) are accessed in sequential order from the lowest to the highest byte (most significant bit first). Read and write block transfers can be stopped after any complete byte transfer. During a write operation, data will not be moved into the registers until the STOP bit is received, at which point, all data received in the block write will be written simultaneously.

For full electrical I²C compliance, it is recommended to use external pull-up resistors for SDATA and SCLK. The internal pull-up resistors have a size of $51k\Omega$ typical.

Curr	ent Read																
S	Dev Addr + R	А	Data X	A	Data X +	1 A	000	А	Data n	А	Р						
Sequ	uential Read																
S	Dev Addr + W	А	Offset Addr X	A	Sr	Dev A	ddr + R	A	Data X	A	Data X +1	А	000	А	Data n	А	Р
Sequ	iential Write																
S	Dev Addr + W	A	Offset Addr X	A	Da	ita X	A	Data X +1	A 0	00	A Data	n	A	>			
	from master from slave to			$Sr = \frac{A}{A} = \frac{1}{2}$	S = start Sr = repeated start A = acknowledge A = non-acknowledge P = stop			NOTE: Data X refers to the data at Offset Addr X, Data X+1 refers to the data at Offset Addr +1, etc.									



Register Description

Table 13: Register Blocks

Register Ranges Offset (Hex)	Register Block Description
00 - 08	Prescaler & PLL Control Registers
09 - 0F	Reserved ^a
10 - 17	Bank A Control Registers
18 - 1F	Bank B Control Registers
20 - 27	Bank C Control Registers
28 - 31	Bank D Control Registers
32 - 37	Reserved
38 - 3C	Reserved
3D - 40	Device Control Registers
41 - 4B	Reserved
4C - 4F	Reserved
50 - FF	Reserved

a. Reserved registers should not be written to and have indeterminate read values.

Table 14: Prescaler & PLL Control Register Bit Field Locations and Descriptions

		Prescaler &	PLL Contro	ol Register Blo	ock Field Loca	ations					
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0			
00	Rsvd	Rsvd			P	S[5:0]					
01		L L		FDP							
02		Rsvd FIN_CTI									
03		Rsvd									
04				Rsvd				M[8]			
05				Μ	[7:0]						
06				F	Rsvd						
07				F	Rsvd						
08		Rsvd CP[4:0]									
		Prescaler & F	PLL Control	Register Bloc	k Field Descr	iptions					
Bit Field Name	Field Type	Default Value	Descriptio	n							
PS[5:0]	R/W	00000b	00h = Rese	erved	requency by th value used (e.		by-4)				
FDP	R/W	1b	Input freque 0 = disable 1 = enable								
FIN_CTL	R/W	0b	0 = PS[5:0]	, FDP and M s		ined by FIN[1:	0] control pins er settings over l	² C			
OSC_LOW	R/W	0b	0 = normal	• •	ntrol selection: Il frequencies d equencies less		up				
M[8:0]	R/W	019h	PLL Feedback divider ratio: 000h - 003h = Reserved (do not use) 004h - 1FFh = divide f _{VCO} by the value								
CP[4:0]	R/W	11001b	PLL Charge Pump Current Control: Icp = 200μA x (CP[4:0] + 1). Max. charge pump current is 6.4 mA. Default setting is 5.2mA: ((25+1) x 200μA).								
Rsvd	R/W	-	Reserved.	Always write 0	to this bit loca	tion. Read val	ues are not defin	ed.			

Table 15: Bank A Control Register Bit Field Locations and Descriptions

		Bank	A Control Re	gister Block	Field Location	IS			
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0	
10	R	svd			N	A[5:0]		÷	
11				I	Rsvd				
12	PD_A				Rsvd			NA_CTL	
13				I	Rsvd			-	
14	PD_QA0		Pa	svd		STY_QA0		QA0[1:0]	
15	PD_QA1			svd		STY_QA1	AMP_QA1[1:0]		
16	PD_QA2		Rs	svd		STY_QA2		QA2[1:0]	
17	PD_QA3		Rs	svd		STY_QA3	AMP_C	QA3[1:0]	
		Bank A	Control Regi	ister Block Fi	ield Descriptio	ons			
Bit Field Name	Field Type	Default Value	e Descriptio	n					
NA[5:0]	R/W	0Dh	Any change toggled. 00 0000b = 00 001b = 00 001b = 00 010b = 00 010b = 00 011b = 00 011b = 00 0110b = 00 100b = 00 100b = 00 101b = 00 110b = 00 110b = 00 111b = 00 111b = 01 0000b = 01 001b = 01 001b = 01 001b = 01 010b = 01 010b = 01 010b = 01 010b = 01 010b =	Reserved +1 +2 +3 +4 +5 +6 +8 +9 +10 +12 +14 +15 +16 +18 +20 +21 +22 +21 +22 +24 +25 +27 +28	s register will n 01 0110b 01 0111b 01 1000b 01 1000b 01 1010b 01 1010b 01 1100b 01 1100b 01 1110b 01 1110b 01 1110b 10 0000b 10 0001b 10 0010b 10 0110b 10 0110b 10 0110b 10 1000b 10 1000b	= +32 = +33 = +35 = +36 = +40 = +42 = +44 = +45 = +48 = +50 = +54 = +55 = +56 = +66 = +64 = +70 = +72 = +80	10 1011b = 10 1100b = 10 1100b = 10 1101b = 10 1110b = 10 1111b = 10 000b = 11 0000b = 11 0010b = 11 0010b = 11 0110b = 11 0110b = 11 1010b = 11 1001b = 11 1001b = 11 1001b = 11 1001b = 11 1001b = 11 1001b = 11 1100b = 11 1100b = 11 1110b = 11 1110b = 11 1110b = 11 1110b = 11 1111b = 11 111b = 11 1	+88 +90 +96 +100 +118 +110 +112 +120 +128 +132 +140 +132 +140 +144 +160 +176 +176 +180 +200 +220 Reserved Reserved Reserved	
PD_A	R/W	0b	0 = Bank A 1 = Bank A to QA outpu	& all QA outp & all QA outp	uts powered-do vering-down the	nd operate norn own - no active n e output bank, it	eceivers should		
NA_CTL	R/W	0b	0 = NA[5:0] control pins	s , PD_A, EN_4	A, STY_Ax and	AMP_Ax[1:0] s AMP_Ax[1:0] s	-	• •	
PD_QAx	R/W	0b	0 = QAx ou		and operates r	normally ve receivers sho	ould be connect	ed to the QA	

	Bank A Control Register Block Field Descriptions										
Bit Field Name	Field Type	Default Value	Description								
STY_QAx	R/W	0b	Output Style for Output QAx: 0 = QAx is LVDS 1 = QAx is LVPECL								
AMP_QAx[1:0]	R/W	00b	Output Amplitude for Output QAx (measured single-ended): 00 = 350mV 01 = 500mV 10 = 750mV 11 = Reserved								
Rsvd	R/W	-	Reserved. Always write 0 to this bit location. Read values are not defined.								

Table 16: Bank B Control Register Bit Field Locations and Descriptions

			T	-	Field Location			
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0
18	R	svd			N	B[5:0]		
19					Rsvd			
1A	PD_B				Rsvd			NB_CTL
1B					Rsvd			
1C	PD_QB0		R	svd		STY_QB0		QB0[1:0]
1D	PD_QB1			lsvd		STY_QB1		QB1[1:0]
1E	PD_QB2		R	lsvd		STY_QB2		QB2[1:0]
1F	PD_QB3		R	lsvd		STY_QB3	AMP_C	QB3[1:0]
		Bank I	B Control Reg	gister Block F	ield Descriptio	ons		
Bit Field Name	Field Type	Default Valu	e Descripti	on				
NB[5:0]	R/W	0Dh	Any chang toggled. 00 0000b 00 001b 00 0010b 00 010b 00 010b 00 010b 00 010b 00 011b 00 0110b 00 1010b 00 1010b 00 1010b 00 1110b 00 110b 00 1110b 00 1110b 00 1110b 00 1110b 00 1110b 01 0000b 01 0001b 01 0010b 01 0100b 01 0101b	= Reserved = +1 = +2 = +3 = +4 = +5 = +6 = +8 = +9 = +10 = +12 = +14 = +15 = +16 = +18 = +20 = +21 = +22 = +24 = +25 = +27	is register will r 01 0110b 01 0111b 01 1000b 01 1001b 01 1010b 01 1010b 01 1010b 01 1101b 01 1100b 01 1110b 01 1111b 10 0000b 10 0011b 10 0100b 10 0110b 10 0110b 10 0111b 10 1000b 10 1001b 10 1001b 10 1001b 10 1001b	= +32 = +33 = +35 = +36 = +40 = +42 = +44 = +45 = +48 = +50 = +54 = +55 = +56 = +60 = +64 = +66 = +70 = +72 = +80	10 1011b = 10 1100b = 10 1100b = 10 1101b = 10 1110b = 10 1111b = 11 0000b = 11 0010b = 11 0010b = 11 0100b = 11 0110b = 11 0110b = 11 1010b = 11 1010b = 11 1010b = 11 1010b = 11 1010b = 11 1000b = 11 1010b = 11 1000b = 11 100	*88 *90 *96 *100 *108 *110 *112 *120 *128 *132 *140 *132 *140 *144 *160 *176 *180 *220 Reserved Reserved Reserved Reserved
PD_B	R/W	0b	0 = Bank	B & all QB out 3 & all QB outp		nd operate norn own - no active r		l be connecto
NB_CTL	R/W	Ob	0 = NB[5:0 control pir	is)], PD_B, EN_	B, STY_Bx and	AMP_Bx[1:0] s AMP_Bx[1:0] s	-	
PD_QBx	R/W	Ob	0 = QBx o 1 = QBx o output. W	utput powered	and operates -down - no acti	normally ve receivers sho t bank, it is reco		

	Bank B Control Register Block Field Descriptions										
Bit Field Name	Field Type	Default Value	Description								
STY_QBx	R/W	0b	Output Style for Output QBx: 0 = QBx is LVDS 1 = QBx is LVPECL								
AMP_QBx[1:0]	R/W	00b	Output Amplitude for Output QBx (measured single-ended): 00 = 350mV 01 = 500mV 10 = 750mV 11 = Reserved								
Rsvd	R/W	-	Reserved. Always write 0 to this bit location. Read values are not defined.								

Table 17: Bank C Control Register Bit Field Locations and Descriptions

A dalaa a a (11aa)	67		T	-	Field Location		D 4	D 0	
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0	
20	R	svd				C[5:0]			
21					Rsvd				
22	PD_C				Rsvd			NC_CT	
23					Rsvd				
24	PD_QC0		R	svd		STY_QC0	AMP_QC0[1:0]		
25	PD_QC1		R	svd		STY_QC1	AMP (QC1[1:0]	
26					Rsvd				
27					Rsvd				
		Denk							
			-		ield Description	ons			
Bit Field Name	Field Type	Default Valu	•	on io for Bank C:					
NC[5:0]	R/W	0Dh	00 0001b 00 0010b 00 0100b 00 0100b 00 0101b 00 0110b 00 0111b 00 1000b 00 1010b 00 1010b 00 1100b 00 1110b 00 1110b 00 1110b 00 1110b 00 1111b 01 0000b 01 0010b 01 0010b 01 0010b 01 0100b	= +2 = +3 = +4 = +5 = +6 = +8 = +9 = +10 = +12 = +12 = +14 = +15 = +16 = +18 = +20 = +21 = +22 = +22 = +24 = +25 = +27	01 0110b 01 0111b 01 1000b 01 1001b 01 1010b 01 1011b 01 1100b 01 1101b 01 1100b 01 1110b 01 1110b 01 1111b 10 0000b 10 0001b 10 0010b 10 0100b 10 0101b 10 0101b 10 1000b 10 1001b 10 1001b	= +32 = +33 = +35 = +36 = +40 = +42 = +44 = +45 = +45 = +48 = +50 = +54 = +55 = +56 = +60 = +66 = +70 = +72 = +80	10 1011b = 10 1100b = 10 1101b = 10 1110b = 10 1111b = 11 0000b = 11 0001b = 11 0010b = 11 0100b = 11 0100b = 11 0110b = 11 0110b = 11 1001b = 11 1001b = 11 1010b = 11 1001b = 11 1001b = 11 1001b = 11 1100b = 11 1100b = 11 1110b = 11 1110b = 11 1111b = 11 11111b = 11 1111b = 11 111b = 11 11b	+90 +96 +100 +108 +110 +112 +120 +128 +132 +140 +144 +160 +176 +180 +200 +220 Reserved Reserved Reserved	
PD_C	R/W	0b	0 = Bank (C & all QC out C & all QC outp		nd operate norn own - no active r		d be connect	
NC_CTL	R/W	Ob	0 = NC[5:0 control pin	s], PD_C, EN_	C, STY_Cx and	I AMP_Cx[1:0] s I AMP_Cx[1:0] s	-		
PD_QCx	R/W	Ob	0 = QCx o 1 = QCx o output. Wh	utput powered	l and operates I-down - no act	normally ive receivers sho t bank, it is reco			

RENESAS

	Bank C Control Register Block Field Descriptions										
Bit Field Name	Field Type	Default Value	Description								
STY_QCx	R/W	0b	Output Style for Output QCx: 0 = QCx is LVDS 1 = QCx is LVPECL								
AMP_QCx[1:0]	R/W	00b	Output Amplitude for Output QCx (measured single-ended): 00 = 350mV 01 = 500mV 10 = 750mV 11 = Reserved								
Rsvd	R/W	-	Reserved. Always write 0 to this bit location. Read values are not defined.								

Table 18: Bank D Control Register Bit Field Locations and Descriptions

	_			-	Field Location			_	
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0	
28				ND_F	FRAC[7:0]				
29				ND_F	RAC[15:8]				
2A				ND_FF	RAC[23:16]				
2B		Rs	/d			ND_F	INT[3:0]		
2C	R	svd			N	D[5:0]			
2D		Rsv	/d			01VF[1:0]	ND_DIV	ND_SR	
25 2E	PD_D				ND_CT				
2E 2F	FD_D				Rsvd				
					Rsvd			B a i / a i	
30	PD_QD0		R	svd		STY_QD0	AMP_C	QD0[1:0]	
31	PD_QD1				Rsvd				
		Bank D	Control Reg	ister Block F	ield Description	ons			
Bit Field Name	Field Type	Default Value	Descriptio	n					
ND_FRAC[23:0]	R/W	600000h			der ratio for fra atio = ND_FRA	ctional divider fo C[23:0] / 2 ²⁴	r Bank D:		
ND_FINT[3:0]	R/W	1001b	Integer portion of divider ratio for fractional divider for Bank D: 0h - 4h= Reserved 5h - Fh = divide by the value used (e.g. 5 = divide-by-5)						
ND[5:0]	R/W	0Dh	Any chang toggled. 00 0000b = 00 0010b = 00 0010b = 00 0110b = 00 0110b = 00 0110b = 00 0110b = 00 1000b = 00 1001b = 00 1010b = 00 1110b = 00 1110b = 00 1110b = 01 110b = 01 0000b = 01 0001b = 01 0010b = 01 0010b = 01 0010b = 01 0110b =	= Reserved = ÷ 1 = ÷ 2 = ÷ 3 = ÷ 4 = ÷ 5 = ÷ 6 = ÷ 8 = ÷ 9 = ÷ 10 = ÷ 12 = ÷ 14 = ÷ 15 = ÷ 16 = ÷ 18 = ÷ 20 = ÷ 21 = ÷ 22 = ÷ 22 = ÷ 24 = ÷ 27 = ÷ 28 11 CMOS output	01 0110b 01 0111b 01 1000b 01 1001b 01 1010b 01 1011b 01 1100b 01 1101b 01 1100b 01 1110b 01 1110b 10 0000b 10 0001b 10 0010b 10 0010b 10 0101b 10 0110b 10 0111b 10 1000b 10 1001b 10 1000b 10 1001b 10 1000b 10 1000b	= \div 32 = \div 33 = \div 35 = \div 36 = \div 40 = \div 42 = \div 44 = \div 45 = \div 48 = \div 50 = \div 54 = \div 55 = \div 56 = \div 60 = \div 64 = \div 70 = \div 72 = \div 80 = \div 84 powered-off or distance of the set of th	10 1011b = 10 1100b = 10 1101b = 10 1110b = 10 1111b = 11 0000b = 11 0001b = 11 0010b = 11 0101b = 11 0101b = 11 0110b = 11 1001b = 11 1001b = 11 1001b = 11 1011b = 11 1100b = 11 1100b = 11 1110b = 11 1111b = 11 1111b = 11 1111b =	+ 88 + 90 + 96 + 100 + 108 + 110 + 112 + 120 + 128 + 120 + 128 + 132 + 140 + 144 + 160 + 176 + 180 + 200 + 220 Reserved Reserved Reserved Reserved Reserved	
ND_DIVF[1:0]	R/W	00ь	Post-divide 00 = ÷1 01 = ÷2 10 = ÷4 11 = Reser		tional divider fo	or Bank D:			

		Bank D (Control Register Block Field Descriptions
Bit Field Name	Field Type	Default Value	Description
ND_DIV	R/W	Ob	Control which divider is used to provide output frequency for Bank D: 0 = Integer divider D (ND configures this) 1 = Fractional mode (ND_FINT, ND_FRAC and ND_DIVF configure this)
ND_SRC	R/W	0b	Output Source Selection for Bank D: 0 = Bank D is driven from the integer or fractional divider as selected by ND_SRC 1 = Bank D is driven from the input reference (after the mux) with f _{IN}
PD_D	R/W	Ob	Power-down Bank D: 0 = Bank D & all QD outputs powered and operate normally 1 = Bank D & all QD outputs powered-down - no active receivers should be connected to QD0 output. QD1 output is in High-Impedance.
ND_CTL	R/W	Bank D Configuration Control: 0 = ND[5:0], ND_FRAC[23:0], ND_FINT[3:0], ND_DIVF[1:0], ND_DIV, ND_SRC, PD_D, EN_D, STY_D0 and AMP_D0[1:0] settings determined by ND[1:0] control pins 1 = ND[5:0], ND_FRAC[23:0], ND_FINT[3:0], ND_DIVF[1:0], ND_DIV, ND_SRC, PD_D, EN_D, STY_D0 and AMP_D0[1:0] settings determined by register settings over I ² C	
PD_QDx	R/W	Ob	Power-down Output QDx: 0 = QD[0:1] outputs powered and operate normally 1 = QD0 output powered-down - no active receivers should be connected to the QD0 output, QD1 output is in High-Impedance. When powering-down the output bank, it is recommended to also write a '1' to the PD_QDx registers.
STY_QD0	R/W	0b	Output Style for Output QD0: 0 = QD0 is LVDS 1 = QD0 is LVPECL
AMP_QD0[1:0]	R/W	00b	Output Amplitude for Output QD0 (measured single-ended): 00 = 350mV 01 = 500mV 10 = 750mV 11 = Reserved
Rsvd	R/W	-	Reserved. Always write 0 to this bit location. Read values are not defined.

Table 19: Device Control Register Bit Field Locations and Descriptions

		Device	Control Re	gister Block F	ield Locations	5		
Address (Hex)	D7	D6	D5	D4	D3	D2	D1	D0
3D	INIT_CLK				Rsvd		I	.
3E	RELOCK				Rsvd			
3F	PB_CAL				Rsvd			
40		Rsvo	d		EN_A	EN_B	EN_C	EN_D
		Device C	Control Reg	ister Block Fie	eld Description	ns		
Bit Field Name	Field Type	Default Value	Descriptio	on				
INIT_CLK	W/O ^a	Ob	done every	/ time a divider	value is change	ed if output divid	s to be synchror der synchronizat on is completed	ion is desired
RELOCK	W/O ^a	0b	Writing a "	1' to this bit loca	ation will cause	the PLL to re-I	ock. This bit will	auto-clear.
PB_CAL	W/O ^a	Ob	Setting this The bias c	urrent is used a for the charge p	rt the calibratio as reference for	r outputs config	precision bias c jured as LVDS a to-clear after the	and for as
EN_A	R/W	1b	0 = Bank A	able control for a outputs QA[0: a outputs QA[0:	3] disabled to I	ogic-low state	(QAx = 0, nQAx	= 1)
EN_B	R/W	1b	0 = Bank E	able control for 3 outputs QB[0: 3 outputs QB[0:	3] disabled to I	ogic-low state	(QBx = 0, nQBx	= 1)
EN_C	R/W	1b	0 = Bank C	able control for C outputs QC[0 C outputs QC[0	1] disabled to	logic-low state	(QCx = 0, nQC>	x = 1)
EN_D	R/W	1b	0 = Bank E Note that i down by th of this bit.	f Bank D is pow e PD_QD1 bit,	1] disabled to l vered down via	the PD_D bit o	(QD0 = 0, nQD0 or the QD1 outputedance regardle	ut is powered
			1 = Bank D	Ooutputs QD[0	1] enabled			

a. These bits are read as '0'. When a '1' is written to them, it will have the indicated effect and then self-clear back to '0'.

Absolute Maximum Ratings

Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 20: Absolute Maximum Ratings

Item	Rating
Supply Voltage, V _{CC}	3.6V
Inputs, V _I OSCI Other Inputs	-0.5V to 3.6V -0.5V to 3.6V
Outputs, V _O (LVCMOS)	-0.5V to 3.6V
Outputs, I _O (LVPECL) Continuous Current Surge Current	50mA 100mA
Outputs, I _O (LVDS) Continuous Current Surge Current	50mA 100mA
Maximum Junction Temperature, t _{JMAX}	125°C
Storage Temperature, T _{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 21: Power Supply DC Characteristics, $V_{CC_x}^{a} = V_{CCOX}^{b} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$,

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{CC_X}	Core Supply Volta	ige		3.135	3.3	3.465	V
V _{CCA_X} c	Analog Supply Vo	ltage		3.135	3.3	3.465	V
V _{CCOX}	Output Supply Vo	Itage		3.135	3.3	3.465	V
ı d	Core	LVPECL	All Outputs Enabled & Terminated ^e		73	100	mA
I _{CC_x} ^d Supply Current	LVDS	All Outputs Enabled & Terminated ^f		73	100	mA	
ı a	Analog	LVPECL	All Outputs Enabled & Terminated ^e		141	169	mA
I _{CCA_x} ^g Supply Current	LVDS	All Outputs Enabled & Terminated ^f		141	167	mA	
		LVPECL	350mV, Outputs Enabled & Terminated ^e		189	226	mA
			500mV, Outputs Enabled & Terminated ^e		183	217	mA
			750mV, Outputs Enabled & Terminated ^e		172	205	mA
			350mV, Outputs Enabled & Terminated ^f		84	103	mA
		LVDS	500mV, Outputs Enabled & Terminated ^f		101	124	mA
ı h	Bank A Output		750mV, Outputs Enabled & Terminated ^f		130	161	mA
I _{CCOA} h	Supply Current		350mV, Outputs Disabled & Unterminated		8	10	mA
		LVPECL	500mV, Outputs Disabled & Unterminated		10	12	mA
			750mV, Outputs Disabled & Unterminated		12	15	mA
		LVDS	350mV, Outputs Disabled & Unterminated		26	32	mA
			500mV, Outputs Disabled & Unterminated		36	43	mA
			750mV, Outputs Disabled & Unterminated		51	62	mA

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
			350mV, Outputs Enabled & Terminated ^e		196	234	mA
		LVPECL	500mV, Outputs Enabled & Terminated ^e		188	224	mA
			750mV, Outputs Enabled & Terminated ^e		177	211	mA
			350mV, Outputs Enabled & Terminated ^f		86	105	mA
		LVDS	500mV, Outputs Enabled & Terminated ^f		103	126	mA
ı h	Bank B Output		750mV, Outputs Enabled & Terminated ^f		132	163	mA
I _{CCOB} h	Supply Current		350mV, Outputs Disabled & Unterminated		9	11	mA
		LVPECL	500mV, Outputs Disabled & Unterminated		10	13	mA
			750mV, Outputs Disabled & Unterminated		13	16	mA
		LVDS	350mV, Outputs Disabled & Unterminated		27	33	mA
			500mV, Outputs Disabled & Unterminated		36	44	mA
			750mV, Outputs Disabled & Unterminated		52	62	mA
		LVPECL	350mV, Outputs Enabled & Terminated ^e		109	131	mA
			500mV, Outputs Enabled & Terminated ^e		106	127	mA
			750mV, Outputs Enabled & Terminated ^e		100	120	mA
			350mV, Outputs Enabled & Terminated ^f		55	67	mA
		LVDS	500mV, Outputs Enabled & Terminated ^f		64	78	mA
ı h	Bank C Output		750mV, Outputs Enabled & Terminated ^f		78	95	mA
I _{CCOC} h	Supply Current		350mV, Outputs Disabled & Unterminated		1	2	mA
		LVPECL	500mV, Outputs Disabled & Unterminated		1	2	mA
			750mV, Outputs Disabled & Unterminated		1	2	mA
			350mV, Outputs Disabled & Unterminated		1	2	mA
		LVDS	500mV, Outputs Disabled & Unterminated		1	2	mA
			750mV, Outputs Disabled & Unterminated		1	2	mA

Table 21: Power Supply DC Characteristics, $V_{CC_x}^{a} = V_{CCOX}^{b} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$, Cont.

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
			350mV, Outputs Enabled & Terminated ^e		91	114	mA
		LVPECL	500mV, Outputs Enabled & Terminated ^e		89	112	mA
Iccop ^h			750mV, Outputs Enabled & Terminated ^e		86	109	mA
			350mV, Outputs Enabled & Terminated ^f		57	69	mA
		LVDS	500mV, Outputs Enabled & Terminated ^f		62	75	mA
	Bank D Output		750mV, Outputs Enabled & Terminated ^f		70	85	mA
	Supply Current	LVPECL	350mV, Outputs Disabled & Unterminated		3	5	mA
			500mV, Outputs Disabled & Unterminated		3	5	mA
			750mV, Outputs Disabled & Unterminated		3	5	mA
		LVDS	350mV, Outputs Disabled & Unterminated		3	5	mA
			500mV, Outputs Disabled & Unterminated		3	5	mA
			750mV, Outputs Disabled & Unterminated		3	5	mA
			350mV, Outputs Enabled & Terminated ^e		385	470	mA
		LVPECL	500mV, Outputs Enabled & Terminated ^e		394	481	mA
ı h	Power Supply Current		750mV, Outputs Enabled & Terminated ^e		407	497	mA
I _{EE} h	for V _{EE}		350mV, Outputs Disabled & Unterminated		233	277	mA
			500mV, Outputs Disabled & Unterminated		236	280	mA
			750mV, Outputs Disabled & Unterminated		241	286	mA

Table 21: Power Supply DC Characteristics, $V_{CC_x}^{a} = V_{CCOX}^{b} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{EE} = 0V$, Cont.

a. V_{CC_x} denotes V_{CC_CP} , V_{CC_CK} , V_{CC_SP} . b. V_{CCOX} denotes V_{CCOA} , V_{CCOB} , V_{CCOD} . c. V_{CCA_x} denotes $V_{CCA_{IN1}}$, $V_{CCA_{IN2}}$, V_{CCA} , $V_{CCA_{XT}}$. d. I_{CC_x} denotes I_{CC_CP} , I_{CC_CK} , I_{CC_SP} . e. Differential outputs terminated 50 Ω to V_{CCOX} - 2V. QD1 output terminated 50 Ω to $V_{CCOD}/2$.

f. Differential outputs terminated 100 Ω across Q and nQ. QD1 output terminated 50 Ω to V_{CCOD}/2.

g. I_{CCA_X} denotes $I_{CCA_IN1,}$ $I_{CCA_IN2,}$ $I_{CCA,}$ $I_{CCA_XT.}$ h. Internal maximum dynamic switching current is included.

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage			0.7 * V _{CC} ^c		3.465	V
V _{IM}	Input Middle Voltage	FIN[1:0], NA[1:0], NB[1:0], NC[1:0], ND[1:0]		0.4 * V _{CC} ^c		0.6 * V _{CC} ^c	V
V _{IL}	Input Low Voltage	1		-0.3		0.3 * V _{CC} ^c	V
I _{IH}	Input High Current	FIN[1:0], NA[1:0], NB[1:0], NC[1:0], ND[1:0]	V _{CC} ^c = V _{IN} = 3.465V			150	μA
I _{IM}	Input Middle Current	FIN[1:0], NA[1:0], NB[1:0], NC[1:0], ND[1:0]	$V_{IN} = V_{CC}^{c} / 2$		±1		μA
I _{IL}	Input Low Current	FIN[1:0], NA[1:0], NB[1:0], NC[1:0], ND[1:0]	V _{CC} ^c = 3.465V, V _{IN} = 0V	-150			μA

Table 22: LVCMOS DC Characteristics for 3-level Pins, $V_{CC_X}^a = V_{CCOX}^b = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$

a. V_{CC_X} denotes V_{CC_CP}, V_{CC_CK}, V_{CC_SP}.

b. V_{CCOX} denotes V_{CCOA} , V_{CCOB} , V_{CCOC} , V_{CCOD} . c. V_{CC} denotes V_{CCA_IN1} , V_{CC_CK} .

Table 23: LVCMOS DC Characteristics for 2-level Pins, $V_{CC_X}^a = V_{CCOX}^b = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$

Symbol	Parameter	Parameter		Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage			0.7 * V _{CC} ^c		3.465	V
V _{IL} Inpu		REF_SEL		-0.3		0.3 * V _{CC} ^c	V
	Input Low Voltage	SDATA, SCLK		-0.3		0.15 * V _{CC} ^c	V
han think Orment	SCLK, SDATA	V _{CC} ^c = V _{IN} = 3.465V			5	μA	
IIH	H Input High Current	REF_SEL	V _{CC} ^c = V _{IN} = 3.465V			150	μA
1		SCLK, SDATA	V _{CC} ^c = 3.465V, V _{IN} = 0V	-150			μA
IIL	Input Low Current	REF_SEL	V _{CC} ^c = 3.465V, V _{IN} = 0V	-5			μA
V _{OH}	Output High Voltage	LOCK	I _{OH} = -4mA	2.2			V
V _{OL}	Output Low Voltage	SDATA, LOCK	I _{OL} = 4mA			0.45	V

a. V_{CC_X} denotes V_{CC_CP}, V_{CC_CK}, V_{CC_SP}. b. V_{CCOX} denotes V_{CCOA}, V_{CCOB}, V_{CCOC}, V_{CCOD}.

c. V_{CC} denotes V_{CC_CK.}

Table 24: Differential Input DC Characteristics, $V_{CC_X}^a = V_{CCOX}^b = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$

			=				
Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I _{IH}	Input High Current	CLK_IN, nCLK_IN	V _{CC} ^c = V _{IN} = 3.465V			150	μA
	Input	CLK_IN	V _{CC} ^c = 3.465V, V _{IN} = 0V	-5			μA
ιL	Low Current	nCLK_IN	V _{CC} ^c = 3.465V, V _{IN} = 0V	-150			μA
V _{PP}	Peak-to-Peak Voltage ^{d, e}	CLK_IN, nCLK_IN		0.2		1.4	V
V _{CMR}	Common Mode Input Voltage ^{d, e}	CLK_IN, nCLK_IN		V _{EE} + 1.1		$V_{CC}^{c} - 0.3$	V

a. V_{CC_X} denotes V_{CC_CP}, V_{CC_CK}, V_{CC_SP}. b. V_{CCOX} denotes V_{CCOA}, V_{CCOB}, V_{CCOC}, V_{CCOD}.

c. V_{CC} denotes V_{CC_CK.}

d. Common mode voltage is defined as the cross point.

e. Input voltage cannot be less than V_{EE} - 300mV or more than V_{CC.}

Table 25: LVPECL Output DC Characteristics (Qmn^a), $V_{CC_X}^b = V_{CCOX}^c = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
		350mV Amplitude setting	V _{CCOX} – 1.1		$V_{CCOX} - 0.8$	
V _{OH}	Output High Voltage ^d	500mV Amplitude setting	V _{CCOX} – 1.1		V _{CCOX} - 0.8	V
		750mV Amplitude setting	V _{CCOX} – 1.1		V _{CCOX} - 0.8	
		350mV Amplitude setting	V _{CCOX} – 1.5		V _{CCOX} – 1.1	
V _{OL}	Output Low Voltage ^d	500mV Amplitude setting	V _{CCOX} – 1.6		V _{CCOX} – 1.3	V
		750mV Amplitude setting	V _{CCOX} – 1.8		V _{CCOX} – 1.5	
		350mV Amplitude setting	280	350	420	
V _{SWING}	Single-ended Peak-to-Peak Output Voltage Swing	500mV Amplitude setting	430	500	570	mV
		750mV Amplitude setting	630	700	770	

a. In this table, Qmn denotes the differential outputs QA[0:3], QB[0:3], QC[0:1] or QD0. Note that QD1 is not included because it is not differential.

b. V_CC_X denotes V_CC_CP, V_CC_CK, V_CC_SP.

c. V_{CCOX} denotes V_{CCOA} , V_{CCOB} , V_{CCOC} , V_{CCOD} .

d. Outputs terminated with 50 Ω to V_{CCOX} – 2V.

RENESAS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
		350mV Amplitude setting	0.27	0.32	0.37	
V _{OD} Differential Output Voltage	500mV Amplitude setting	0.39	0.46	0.53	V	
		750mV Amplitude setting	0.62	0.69	0.76	
ΔV_{OD}	V _{OD} Magnitude Change				50	mV
		350mV Amplitude setting	1.9	2.3	2.7	
V _{OS} Offset Voltage ^{d, e, f}	Offset Voltage ^{d, e, f}	500mV Amplitude setting	1.8	2.2	2.6	V
		750mV Amplitude setting	1.7	2.1	2.5	
ΔV_{OS}	V _{OS} Magnitude Change				50	mV

Table 26: LVDS Output DC Characteristics (Qmn^a), $V_{CC X}^{b} = V_{CCOX}^{c} = 3.3V \pm 5\%$, $T_{A} = -40^{\circ}C$ to +85°C, $V_{EE} = 0V$

a. In this table, Qmn denotes the differential outputs QA[0:3], QB[0:3], QC[0:1] or QD0. Note that QD1 is not included because it is not differential.

b. V_{CC_X} denotes V_{CC_CP} , V_{CC_CK} , V_{CC_SP} . c. V_{CCOX} denotes V_{CCOA} , V_{CCOB} , V_{CCOC} , V_{CCOD} . d. No external DC pulldown resistor.

e. Loading condition is with 100Ω across the differential output.

f. Offset voltage (V_OS) changes with supply voltage V_CCOX.

Table 27: Crystal Characteristics

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation			Fundamenta		
Frequency		10		50	MHz
Equivalent Spring Desistance (ESD)	C _L = 12pF			60	Ω
Equivalent Series Resistance (ESR)	C _L = 18pF		15	30	Ω
Load Capacitance (CL)			12		pF
Maximum Crystal Drive Level			200		μW
Frequency Stability (total)		-100		100	ppm

AC Electrical Characteristics

Table 28: AC Characteristics, ${}^{a}V_{CC}$, ${}^{b}=V_{CCOY}{}^{c}=3.3V+5\%$, $T_{A}=-40^{\circ}C$ to +85°C, $V_{FF}=0V$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f _{VCO}	VCO Frequency			2400 5		2500 200	MHz MHz
f _{PFD}	Phase / Frequenc Frequency	y Detector					
f _{OUT}	Output Frequency	QA[0:3] nQA[0:3] QB[0:3] nQB[0:3] QC[0:1] nQC[0:1]		10.91		2500	MHz
		QD0, nQD0	Integer Divider Selected	10.91		2500	MHz
			Fractional Divider Selected	20		138	MHz
		QD1	Integer Divider Selected	10.91		250	MHz
			Fractional Divider Selected	20		138	MHz
<i>t</i> sk(b)	Bank Skew ^{d, e, f}	Bank A	Same Frequency and Output Type Only valid for skew between outputs in the same bank			45	
		Bank B				45	ps
		Bank C				20	
t _R / t _F	Output Rise/Fall Time	QA[0:3] nQA[0:3] QB[0:3] nQB[0:3] QC[0:1] nQC[0:1]	30% to 70%	30	60	110	ps
		QD0, nQD0	30% to 70%	30	90	200	
		QD1	30% to 70%	220	375	600	
odc	Output Duty Cycle ^g	QA[0:3] nQA[0:3] QB[0:3] nQB[0:3] QC[0:1] nQC[0:1], QD0, nQD0	$F_{OUT} \le 1250MHz$	45	50	55	%
			F _{OUT} > 1250MHz	40	50	60	%
		QD1	F _{OUT} < 156.25MHz	45	50	55	%
			F _{OUT} ≥ 156.25MHz	40	50	60	%
t _{LOCK}	PLL Lock Time ^h	1			40	100	ms

a. Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

b. V_{CC_X} denotes V_{CC_CP} , V_{CC_CK} , V_{CC_SP} . c. V_{CCOX} denotes V_{CCOA} , V_{CCOB} , V_{CCOC} , V_{CCOD} .

d. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

e. This parameter is defined in accordance with JEDEC Standard 65.

f. This parameter is guaranteed by characterization. Not tested in production

g. Duty Cycle of bypassed signals (input reference clock or crystal input) is not adjusted by the device.

h. PLL Lock Time is defined as time from input clock availability to frequency locked output. The following loop filter component values may be used: R_Z = 221Ω, C_Z = 4.7µF C_P = 30pf. Refer to Applications Information.

Table 29: Qmn^a and QD1 Phase Noise and Jitter Characteristics, $V_{CC_X}^{b} = V_{CCOX}^{c} = 3.3V+5\%$, $T_A = -40^{\circ}C$ to $+85^{\circ}C^{d}$, e, f, g, h, i

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
₫it(Ø) ^j	RMS Phase Jitter Random	Qmn = 156.25MHz ^k	Integration Range: 12kHz – 20MHz		87	110	fs
	RMS Phase Jitter Random	Qmn = 125MHz	Integration Range: 12kHz – 20MHz		84		fs
	RMS Phase Jitter Random	Qmn = 100MHz	Integration Range: 12kHz – 20MHz		94		fs
	RMS Phase Jitter Random	Qmn = 25MHz	Integration Range: 12kHz – 5MHz		126		fs
	RMS Phase Jitter Random	QD0 = 133.33MHz (fractional) ^I	Integration Range: 12kHz – 20MHz		180		fs
	RMS Phase Jitter Random	QD1= 125MHz	Integration Range: 12kHz – 20MHz		170		fs
	RMS Phase Jitter Random ^m	QAn = 125MHz	Integration Range: 12kHz – 20MHz		85		fs
		QBn = 100MHz	Integration Range: 12kHz – 20MHz		88		fs
		QCn = 25MHz	Integration Range: 12kHz – 5MHz		137		fs
		QD0 = 133.33MHz (fractional)	Integration Range: 12kHz – 20MHz		170		fs
Φ _N (10) ⁿ	Single-Side Band Noise Power, 10Hz from Carrier		Qmn = 156.25MHz		-75.1		dBc/Hz
Φ _N (100) ⁿ	Single-Side Band Noise Power, 100Hz from Carrier		Qmn = 156.25MHz		-109.6		dBc/Hz
Φ _N (1k) ⁿ	Single-Side Band Noise Power, 1kHz from Carrier		Qmn = 156.25MHz		-128.9		dBc/Hz
Φ _N (10k) ⁿ	Single-Side Band Noise Power, 10kHz from Carrier		Qmn = 156.25MHz		-137.6		dBc/Hz
Φ _N (100k) ⁿ	Single-Side Band Noise Power, 100kHz from Carrier		Qmn = 156.25MHz		-143.0		dBc/Hz
Φ _N (1M) ⁿ	Single-Side Band Noise Power, 1MHz from Carrier		Qmn = 156.25MHz		-157.5		dBc/Hz
Φ _N (10M) ⁿ	Single-Side Band 10MHz from Carri		Qmn = 156.25MHz		-163.1		dBc/Hz
Φ _N (∞) ⁿ	Noise Floor (≥30	MHz from Carrier)	Qmn = 156.25MHz		-163.1		dBc/Hz

a. In this table, Qmn denotes the differential outputs QA[0:3], QB[0:3], QC[0:1] or QD0. Note that QD1 is not included because it is not differential.

b. V_{CC_X} denotes V_{CC_CP}, V_{CC_CK}, V_{CC_SP}. c. V_{CCOX} denotes V_{CCOA}, V_{CCOB}, V_{CCOC}, V_{CCOD}.

d. Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

e. All outputs enabled and configured for the same output frequency unless otherwise noted.

f. Characterized using a 50MHz, C_L = 18pF crystal, unless otherwise noted.

g. Measured on Qmn configured as ÷16 and ÷20.

h. V_{CCA} requires a voltage regulator. Voltage supplied to V_{CCA} should be derived from a regulator with a typical power supply rejection ratio of 80dB at 1kHz and ultra low noise generation with a typical value of $3nV/\sqrt{Hz}$ at 10kHz and $7nV/\sqrt{Hz}$ at 1kHz.

i. Characterized with 750mV output voltage swing configuration for all differential outputs.



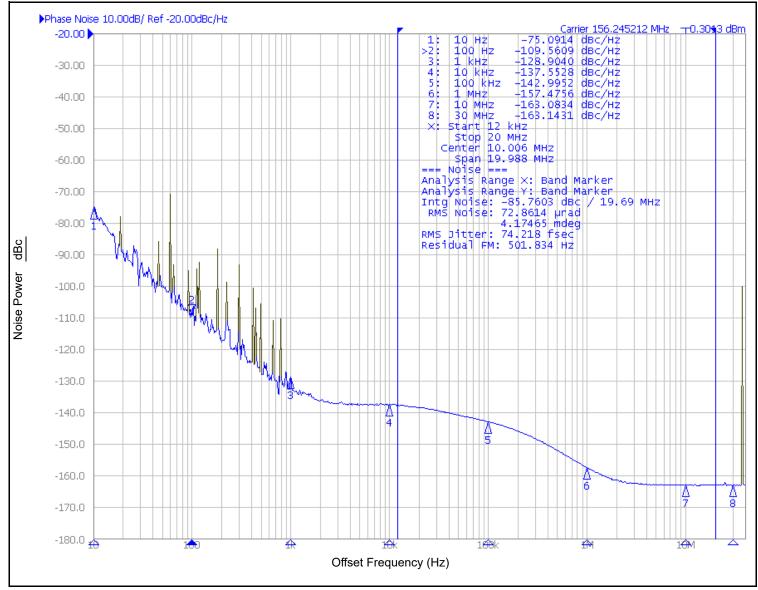
j. The following loop filter component values were used: R_Z = 221Ω, C_Z = 4.7µF, CP = 30pF. PLL Charge Pump Current Control set at 5.2mA.

k. Characterized using a 31.25MHz, C_L = 18pF crystal, (FOX P/N FX277LF-31.25-1).

I. QAx = 156.25MHz, QBx = 156.25MHz, QCx = 156.25MHz.

m. QAx = 156.25MHz, QBx = 100MHz, QCx = 25MHz, QD0 = 133.33MHz (fractional).

n. Measured using a 50MHz, 12pF crystal as input reference. The following loop filter components were used: $R_Z = 150\Omega$, $C_Z = 0.1\mu$ F, CP = 200pF. PLL Charge Pump Current Control set at 6.4mA.

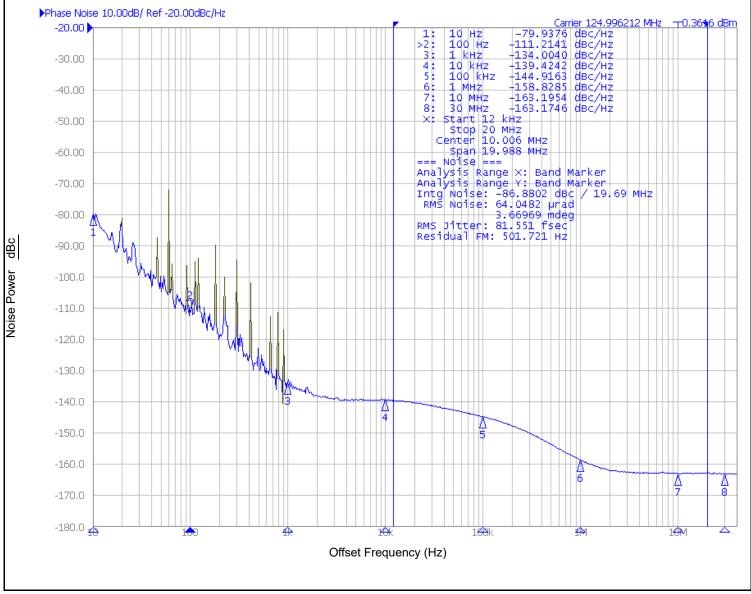


Typical Phase Noise at 156.25MHz^a

a: Measured using a 50MHz, 12pF crystal as input reference. The following loop filter components were used: $R_Z = 150\Omega$, $C_Z = 0.1\mu$ F, CP = 200pF. PLL Charge Pump Current Control set at 6.4mA.



Typical Phase Noise at 125MHz^a



a. Measured using a 50MHz, 12pF crystal as input reference. The following loop filter components were used: $R_Z = 150\Omega$, $C_Z = 0.1\mu$ F, CP = 200pF. PLL Charge Pump Current Control set at 6.4mA.



Applications Information

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pull-up and/or pull-down resistors; additional resistance is not required but can be added for additional protection. A $1k\Omega$ resistor can be used.

Outputs:

LVPECL Outputs

All unused LVPECL outputs should be left floating. It is recommended that there is no trace attached.

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating there should be no trace attached.

LVCMOS Outputs

QD1 output can be left floating if unused. There should be no trace attached.

Overdriving the XTAL Interface

The OSCI input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The OSCO pin can be left floating. The amplitude of the input signal should be between 500mV and 1.2V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 3* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals 90 Ω . In addition, matched termination at the crystal input will further attenuate the signal. This can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50 Ω applications, R1 and R2 can be 100 Ω . This can also be accomplished by removing R1 and changing R2 to 50 Ω . The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver.

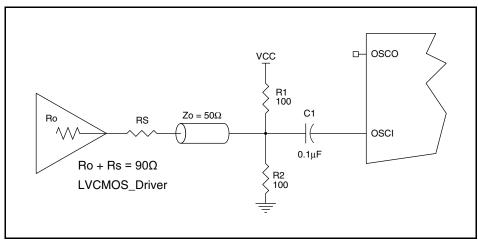


Figure 3: General Diagram for LVCMOS Driver to XTAL Input Interface

Figure 4 shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the OSCI input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

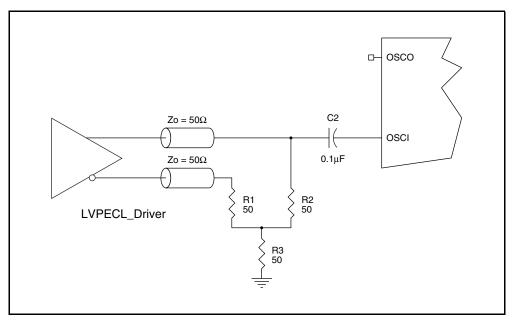


Figure 4: General Diagram for LVPECL Driver to XTAL Input Interface

Wiring the Differential Input to Accept Single-Ended Levels

Figure 5 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_1 = V_{CC}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V_1 in the center of the input voltage swing. For example, if the input clock swing is 2.5V and V_{CC} = 3.3V, R1 and R2 value should be adjusted to set V_1 at 1.25V. The values below are for when both the single ended swing and V_{CC} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, R3 and R4 in parallel should equal the transmission line impedance. For most 50 Ω applications, R3 and R4 can be 100 Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver.

When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than V_{CC} + 0.3V. Suggested edge rate faster than 1V/ns. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

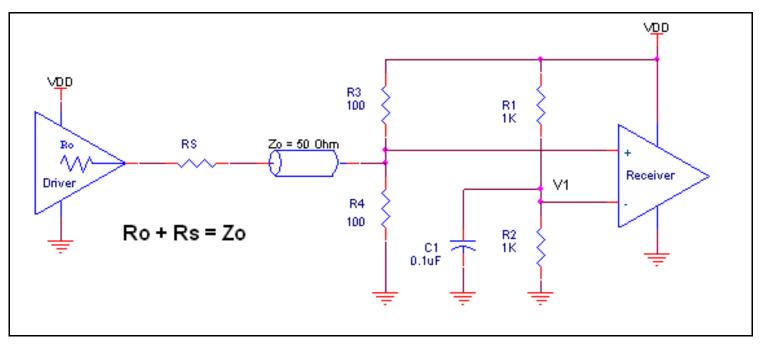
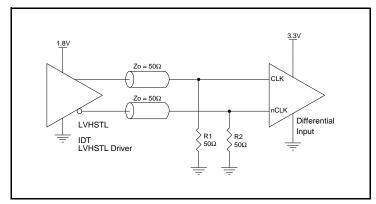


Figure 5: Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

3.3V Differential Clock Input Interface

CLK/nCLK accepts LVDS, LVPECL, LVHSTL, HCSL and other differential signals. Both V_{SWING} and V_{OH} must meet the V_{PP} and V_{CMR} input requirements. *Figure 6* to *Figure 10* show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only.

Please consult with the vendor of the driver component to confirm the driver termination requirements. For example, in *Figure 6*, the input termination applies for IDT open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.





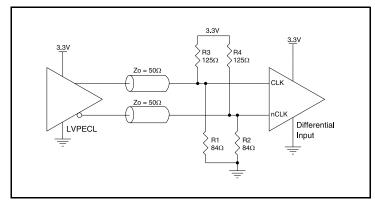


Figure 7: CLK/nCLK Input Driven by a 3.3V LVPECL Driver

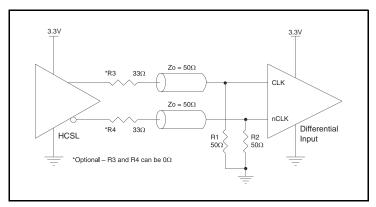


Figure 8: CLK/nCLK Input Driven by a 3.3V HCSL Driver

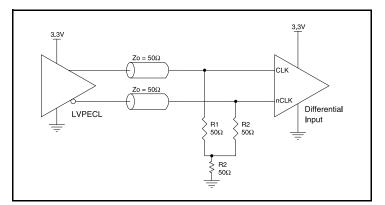


Figure 9: CLK/nCLK Input Driven by a 3.3V LVPECL Driver

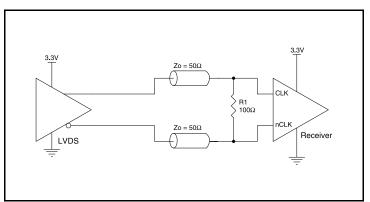


Figure 10: CLK/nCLK Input Driven by a 3.3V LVDS Driver

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90 Ω and 132 Ω . The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard termination schematic as shown in *Figure 11* can be used with either type of output structure. *Figure 12*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.

Refer to Figure 13, Figure 14 and Figure 15 for additional details on the recommended termination schemes.

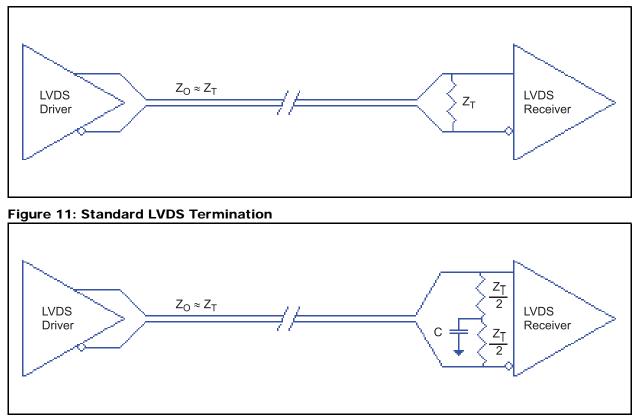
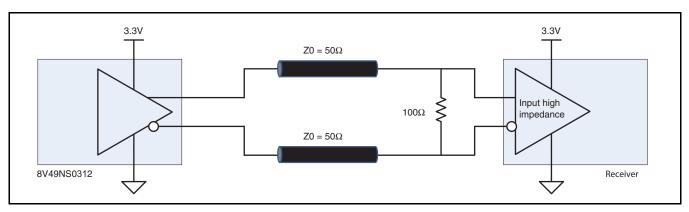
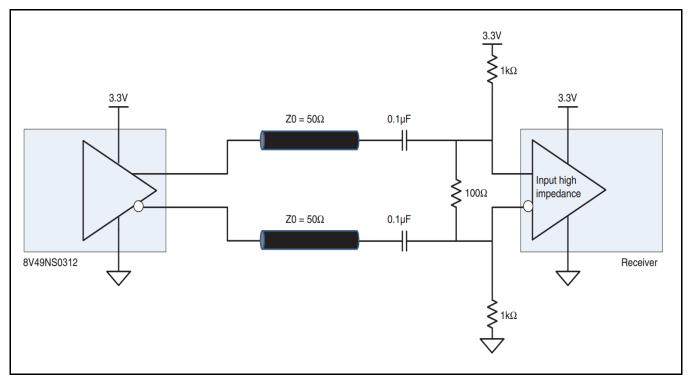


Figure 12: Optional LVDS Termination











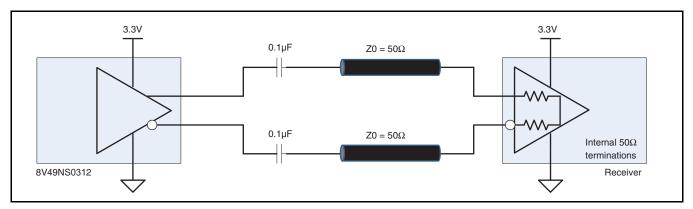


Figure 15: AC Termination for LVDS outputs used with an Input Clock Receiver with Internal 50 Ω Terminations and DC Bias.

Termination for 3.3V LVPECL Outputs

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines. The differential outputs generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive 50Ω transmission lines. Matched impedance techniques should be used to maximize

operating frequency and minimize signal distortion. *Figure 16 and Figure 17* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

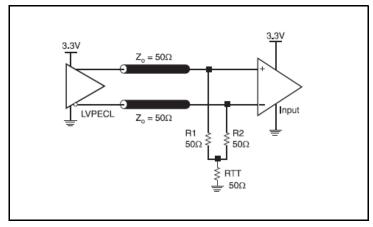


Figure 16: 3.3V LVPECL Output Termination

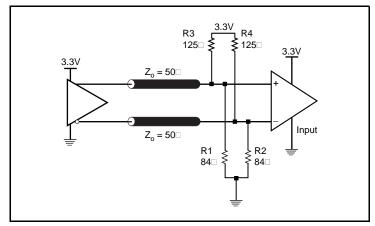


Figure 17: 3.3V LVPECL Output Termination

Figure 16 and Figure 19 show two different LVPECL termination schemes for 750mV amplitude setting which are recommended only as guidelines. Recommended values of R1/R2/R3/R4 for LVPECL termination (Figure 19; Thevenin Equivalent) for 350mV and 500mV amplitude settings can be found in the following table.

Table 1. LVPECL Output Termination, V_{CCOX} = 3.3V ±5%

Test Conditions	Bias Voltage	R 1 [Ω]	R2 [Ω]	R3 [Ω]	R 4 [Ω]
350mV Amplitude Setting	V _{CCOX} – 1.6V	105	105	97.6	97.6
500mV Amplitude Setting	V _{CCOX} – 1.75V	95.3	95.3	107	107
750mV Amplitude Setting	$V_{CCOX} - 2.0V$	84	84	125	125

With a fast ramp up VDD, power-up to lock time is:

- When CR (pin 25) = 1.0uF, typical lock time is around 108ms
- When CR (pin 25) = 0.1uF, typical lock time is around 30ms

VFQFPN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 18.* The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as "heat pipes". The number of vias (i.e. "heat pipes") are application specific and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally/ Electrically Enhance Leadframe Base Package, Amkor Technology.

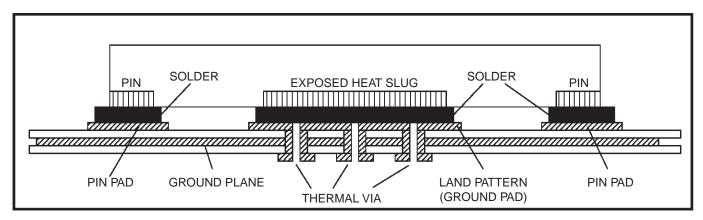


Figure 18: P.C. Assembly for Exposed Pad Thermal Release Path - Side View (drawing not to scale)



Schematic Layout

Figure 19 shows an example 8V49NS0312 application schematic operating the device at V_{CC} = 3.3V. This example focuses on functional connections and is not configuration specific. Refer to the pin description and functional tables in the datasheet to ensure that the logic control inputs are properly set for the application.

To demonstrate the range of output stage configurations possible, the application schematic assumes that the 8V49NS0312 is programmed over I²C. For alternative DC coupled LVPECL options please see IDT Application Note, AN-828; for AC coupling options use IDT Application Note, AN-844.

For a 12pF parallel resonant crystal, tuning capacitors C145 and C146 are recommended for frequency accuracy. Depending on the parasitic of the printed circuit board layout, these values might require a slight adjustment to optimize the frequency accuracy. Crystals with other load capacitance specifications can be used. This will require adjusting C145 and C146. For this device, the crystal tuning capacitors are required for proper operation.

Crystal layout is very important to minimize capacitive coupling between the crystal pads and leads and other metal in the circuit board. Capacitive coupling to other conductors has two adverse effects; it reduces the oscillator frequency leaving less tuning margin and noise coupling from power planes and logic transitions on signal traces can pull the phase of the crystal resonance, inducing jitter. Routing I²C under the crystal is a very common layout error, based on the assumption that it is a low frequency signal and will not affect the crystal oscillation. In fact, I²C transition times are short enough to capacitively couple into the crystal-oscillator loop if they are routed close enough to the crystal traces.

In layout, all capacitive coupling to the crystal from any signal trace is to be minimized, that is to the OSCI and OSCO pins, traces to the crystal pads, the crystal pads and the tuning capacitors. Using a crystal on the top layer as an example, void all signal and power layers under the crystal connections between the top layer and the ground plane used by the 8V49NS0312. Then calculate the parasitic capacity to the ground and determine if it is large enough to preclude tuning the oscillator. If the coupling is excessive, particularly if the first layer under the crystal is a ground plane, a layout option is to void the ground plane and all deeper layers until the next ground plane is reached. The ground connection of the tuning capacitors should first be made between the capacitors on the top layer, then a single ground via is dropped to connect the tuning cap ground to the ground plane as close to the 8V49NS0312 as possible as shown in the schematic.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 8V49NS0312 provides separate power supplies to isolate any high switching noise from coupling into the internal PLL.

In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. The ferrite bead and the 0.1uF capacitor in each power pin filter should always be placed on the device side of the board. The other components can be on the opposite side of the PCB if space on the top side is limited. Pull up and pull down resistors to set configuration pins can all be placed on the PCB side opposite the device side to free up device side area if necessary.

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. Depending on the application, the filter may need to be adjusted to get a lower cutoff frequency to adequately attenuate low-frequency noise. Additionally, good general design practices for power plane voltage stability suggest adding bulk capacitance in the local area of all devices.

For additional layout recommendations and guidelines, contact clocks@idt.com.

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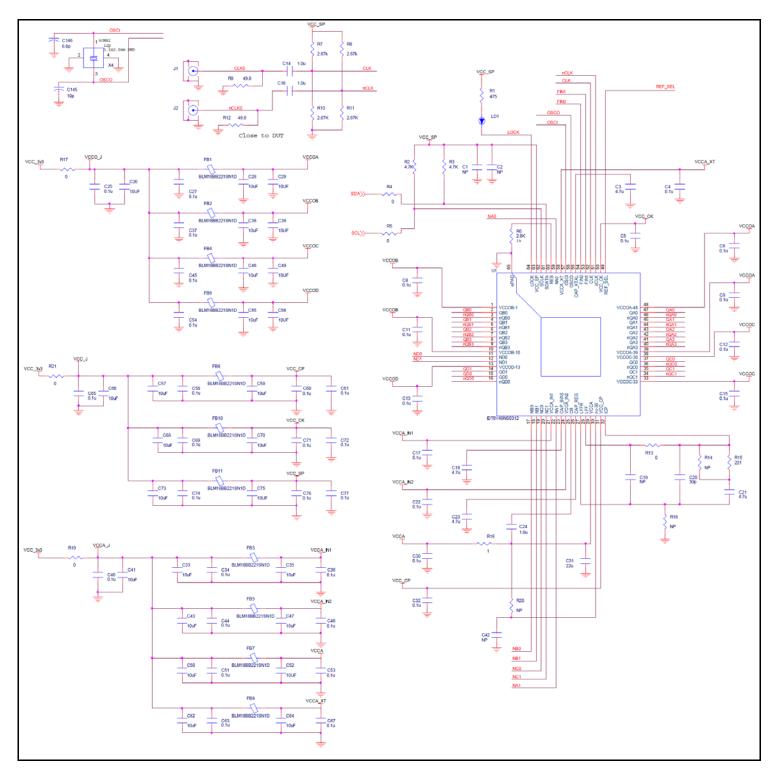


Figure 19: 8V49NS0312 Application Schematic

Power Dissipation and Thermal Considerations

The 8V49NS0312 is a multi-functional, high speed device that targets a wide variety of clock frequencies and applications. Since this device is highly programmable with a broad range of features and functionality, the power consumption will vary as each of these features and functions is enabled.

The 8V49NS0312 device was designed and characterized to operate within the ambient industrial temperature range of -40°C to +85°C. The ambient temperature represents the temperature around the device, not the junction temperature. When using the device in extreme cases, such as maximum operating frequency and high ambient temperature, external air flow may be required in order to ensure a safe and reliable junction temperature. Extreme care must be taken to avoid exceeding 125°C junction temperature.

The power calculation examples below were generated using a maximum ambient temperature and supply voltage. For many applications, the power consumption will be much lower. Please contact IDT technical support for any concerns on calculating the power dissipation for your own specific configuration.

Example 1. LVPECL, 750mV Output Swing

This section provides information on power dissipation and junction temperature when the device differential outputs are configured for LVPECL level, 750mV output swing. Equations and example calculations are also provided.

Output	Output Style	Output Swing
QA0	LVPECL	750mV
QA1	LVPECL	750mV
QA2	LVPECL	750mV
QA3	LVPECL	750mV
QB0	LVPECL	750mV
QB1	LVPECL	750mV
QB2	LVPECL	750mV
QB3	LVPECL	750mV
QC0	LVPECL	750mV
QC1	LVPECL	750mV
QD0	LVPECL	750mV
QD1	LVCMOS	N/A

 Table 30: Power Calculations Configuration #1

1a. Power Dissipation.

The total power dissipation is the sum of the core power plus the power dissipated due to output loading. The following is the power dissipation for V_{CC} = 3.465V, which gives worst case results.

- Power(core)_{MAX} = V_{CC_MAX} * I_{EE_MAX} = 3.465V * 497mA = 1722.1mW
- Power(LVPECL outputs)_{MAX} = 34.2mW/Loaded Output pair. Refer to Section 1c. If all outputs are loaded, the total power is 11 * 34.2mW = 376.2mW
- Power (LVCMOS output)_{MAX}(Power dissipation due to loading 50Ω to V_{CCO} / 2) Output Current: I_{OUT} = V_{CCOD_MAX} / [2 * (50Ω + R_{OUT})] = 3.465V / [2 * (50Ω + 30Ω)] = 21.66mA Power Dissipation on the R_{OUT}: Power (R_{OUT}) = R_{OUT} * (I_{OUT})² = 30Ω * (21.66mA)² = 14.07mW
- Total Power_{MAX} = Power(core) + Power (LVPECL outputs) + Power (LVCMOS output) = 1722.1mW + 376.2mW +14.07mW = 2112.37mW = 2.112W

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1b. Junction Temperature.

Junction temperature, T_J , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_J , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_J is as follows: T_J = T_A + P_D * θ_{JA} :

 T_J = Junction Temperature

T_A = Ambient Temperature

 P_D = Power Dissipation (W) in desired operating configuration

 θ_{JA} = Junction-to-Ambient Thermal Resistance

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance must be used. Assuming no air flow and a multi-layer board, the appropriate value is 15.6°C/W per *Table 32*.

Therefore, assuming $T_A = 85^{\circ}C$ and all outputs switching, T_J will be:

85°C + 2.112W * 15.6°C/W = 117.95°C. This is below the limit of 125°C.

This calculation is only an example. T_J will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

1c. Power Dissipation due to output loading.

The purpose of this section is to calculate the power dissipation for the LVPECL output pair.

LVPECL output driver circuit and termination are shown in Figure 20.

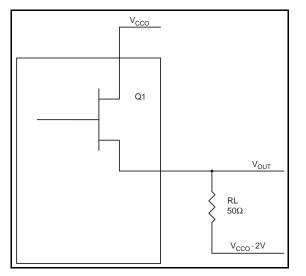


Figure 20: LVPECL Driver Circuit and Termination

To calculate worst case power dissipation at the output(s), use the following equations which assume a 50 Ω load, and a termination voltage of V_{CCOX} - 2V. These are typical calculations.

- For logic high, $V_{OUT} = V_{OH_MAX} = V_{CCOX_MAX} 0.8V$ ($V_{CCOX_MAX} - V_{OH_MAX}$) = 0.8V
- For logic low, $V_{OUT} = V_{OL_MAX} = V_{CCOX_MAX} 1.5V$ ($V_{CCOX_MAX} - V_{OL_MAX}$) = 1.5V

Pd_H is the power dissipation when the output drives high.

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Pd_L is the power dissipation when the output drives low.

 $Pd_H = [(Voh_max - (Vccox_max - 2V))/RL] * (Vccox_max - Voh_max) = [(2V - (Vccox_max - Voh_max))/RL] * (Vccox_max - Voh_max) = [(2V - 0.8V)/50\Omega] * 0.8V = 19.2mW$

 $Pd_L = [(Vol_max - (Vccox_max - 2V))/RL] * (Vccox_max - Vol_max) = [(2V - (Vccox_max - Vol_max))/RL] * (Vccox_max - Vol_max) = [(2V - 1.5V)/50\Omega] * 1.5V = 15mW$

Total Power Dissipation per output pair = Pd_H + Pd_L = 34.2mW

Example 2. LVDS, 350mV Output Swing

This section provides information on power dissipation and junction temperature when the device differential outputs are configured for LVDS levels, 350mV output swing. Equations and example calculations are also provided.

Output	Output Style	Output Swing
QA0	LVDS	350mV
QA1	LVDS	350mV
QA2	LVDS	350mV
QA3	LVDS	350mV
QB0	LVDS	350mV
QB1	LVDS	350mV
QB2	LVDS	350mV
QB3	LVDS	350mV
QC0	LVDS	350mV
QC1	LVDS	350mV
QD0	LVDS	350mV
QD1	LVCMOS	N/A

Table 31: Power Calculations Configuration #2

2a. Power Dissipation.

The total power dissipation is the sum of the core power plus the power dissipation due to output loading. The following is the power dissipation for $V_{CCX} = V_{CCA} = V_{CCOX} = 3.3V + 5\% = 3.465V$, which gives worst case results.

Power_{MAX} = V_{CCX_MAX} * I_{CCX_MAX} + V_{CCA_X_MAX} * I_{CCA_X_MAX} + V_{CCOX_MAX} * I_{CCOX_MAX} * I_{CCOX_MAX}

= 3.465V * 100mA + 3.465V * 167mA + 3.465V (103mA + 105mA + 67mA + 69mA)

= 346.5mW + 578.66mW + 1191.96mW = 2117.12mW = 2.117W



2b. Junction Temperature.

Junction temperature, T_J , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_J , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_J is as follows: $T_J = T_A + P_D * \theta_{JA}$:

T_J = Junction Temperature

T_A = Ambient Temperature

P_D = Power Dissipation (W) in desired operating configuration

 θ_{JA} = Junction-to-Ambient Thermal Resistance

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance must be used. Assuming no air flow and a multi-layer board, the appropriate value is 15.6°C/W per *Table 32*.

Therefore, assuming $T_A = 85^{\circ}C$ and all outputs switching, T_J will be:

85°C + 2.117W * 15.6°C/W = 118.03°C. This is below the limit of 125°C.

This calculation is only an example. T_J will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Reliability Information

Table 32: Thermal Resistance Table for 64-pin VFQFN Package

Symbol	Thermal Parameter	Condition	Value	Unit
θ_{JA}^{a}	Junction-to-Ambient	No air flow	15.6	°C/W
θ_{JC}	Junction-to-Case		15.3	°C/W
θ_{JB}	Junction-to-Board		0.6	°C/W

a. Theta J_A (θ_{JA}) values calculated using an 8-layer PCB (114.3mm x 101.6mm), with 2oz. (70µm) copper plating on all 8 layers, with ePad connected to 4 ground planes.

Transistor Count

The transistor count for the 8V49NS0312 is: 143,063

Package Outline Drawings

The package outline drawings are appended at the end of this document and are accessible from the link below. The package information is the most current data available.

www.idt.com/document/psc/64-vfqfpn-package-outline-drawing-90-x-90-x-09-mm-body-05mm-pitch-epad-60-x-60-mm-nlg64p5



Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8V49NS0312NLGI	IDT8V49NS0312NLGI	64-VFQFPN, Lead-Free	Tray	-40°C to +85°C
8V49NS0312NLGI8	IDT8V49NS0312NLGI	64-VFQFPN, Lead-Free	Tape & Reel	-40°C to +85°C

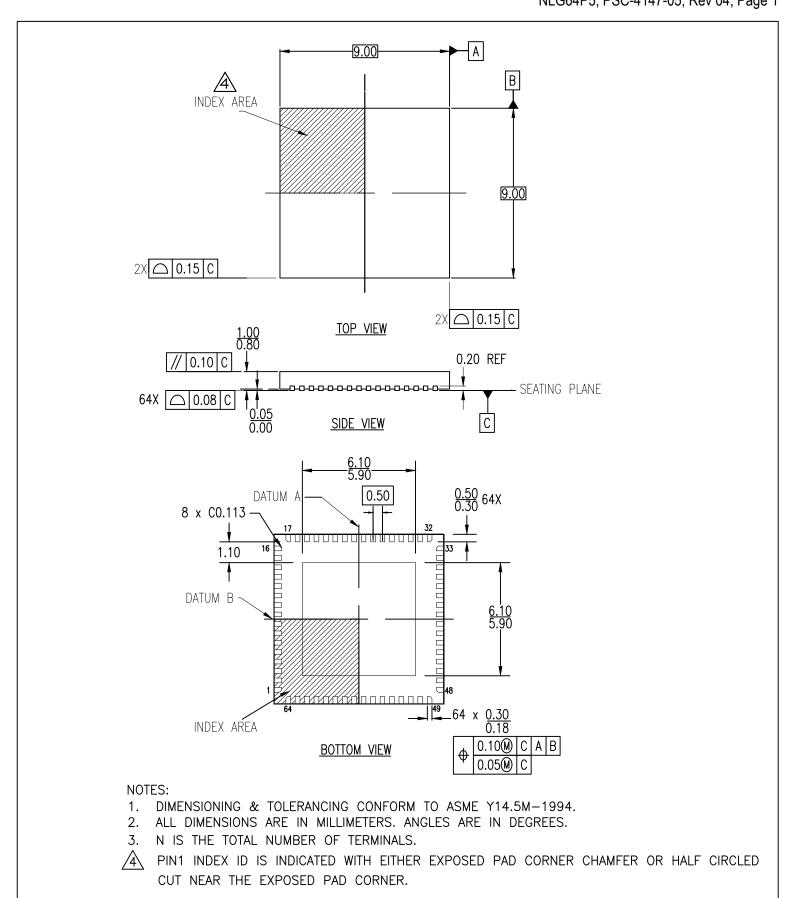
Revision History

Revision Date	Description of Change
April 24, 2019	Updated Overdriving the XTAL Interface
	Updated Termination for 3.3V LVPECL Outputs
	 Updated the Package Outline Drawings; however, no mechanical changes
November 14, 2017	 Updated the QD fractional output divider's maximum frequency to 138MHz to meet period jitter compliance (see Table 28)
	 Updated the Package Outline Drawings; however, no mechanical changes
	Completed other minor changes
September 2, 2016	Page 32, Table 27 Crystal Characteristics - added additional spec to Equivalent Series Resistance row.
August 1, 2016	Page 50, Power Dissipation due to output loading typographical error replaced "-" with "=": For logic low, V _{OUT} = V _{OL_MAX} = V _{CCOX_MAX} - 1.5V, (V _{CCOX_MAX} - V _{OL_MAX}) = 1.5V.
July 11, 2016	Initial release.



64-VFQFPN, Package Outline Drawing

9.0 x 9.0 x 0.9 mm Body, 0.5mm Pitch, Epad 6.0 x 6.0 mm NLG64P5, PSC-4147-05, Rev 04, Page 1





64-VFQFPN, Package Outline Drawing

9.0 x 9.0 x 0.9 mm Body, 0.5mm Pitch, Epad 6.0 x 6.0 mm NLG64P5 , PSC-4147-05, Rev 04, Page 2

